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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Ξ·ΧΕΙ

Details	
Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	48
Program Memory Size	96KB (96K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 12x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LFQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f100lfafb-50

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Pin	Package	Data	Fields of	(5/12) Ordering Part Number
count		flash	Application	
48 pins	48-pin plastic	Mounted	A	R5F100GAAFB#V0, R5F100GCAFB#V0, R5F100GDAFB#V0,
	LFQFP (7 \times 7 mm,			R5F100GEAFB#V0, R5F100GFAFB#V0, R5F100GGAFB#V0,
	0.5 mm pitch)			R5F100GHAFB#V0, R5F100GJAFB#V0, R5F100GKAFB#V0,
				R5F100GLAFB#V0
				R5F100GAAFB#X0, R5F100GCAFB#X0, R5F100GDAFB#X0,
				R5F100GEAFB#X0, R5F100GFAFB#X0, R5F100GGAFB#X0,
				R5F100GHAFB#X0, R5F100GJAFB#X0, R5F100GKAFB#X0,
				R5F100GLAFB#X0
			D	R5F100GADFB#V0, R5F100GCDFB#V0, R5F100GDDFB#V0,
				R5F100GEDFB#V0, R5F100GFDFB#V0, R5F100GGDFB#V0,
				R5F100GHDFB#V0, R5F100GJDFB#V0, R5F100GKDFB#V0,
				R5F100GLDFB#V0
				R5F100GADFB#X0, R5F100GCDFB#X0, R5F100GDDFB#X0,
				R5F100GEDFB#X0, R5F100GFDFB#X0, R5F100GGDFB#X0,
				R5F100GHDFB#X0, R5F100GJDFB#X0, R5F100GKDFB#X0,
				R5F100GLDFB#X0
			G	R5F100GAGFB#V0, R5F100GCGFB#V0, R5F100GDGFB#V0,
				R5F100GEGFB#V0, R5F100GFGFB#V0, R5F100GGGFB#V0,
				R5F100GHGFB#V0, R5F100GJGFB#V0
				R5F100GAGFB#X0, R5F100GCGFB#X0, R5F100GDGFB#X0,
				R5F100GEGFB#X0, R5F100GFGFB#X0, R5F100GGGFB#X0,
				R5F100GHGFB#X0, R5F100GJGFB#X0
		Not	А	R5F101GAAFB#V0, R5F101GCAFB#V0, R5F101GDAFB#V0,
		mounted		R5F101GEAFB#V0, R5F101GFAFB#V0, R5F101GGAFB#V0,
				R5F101GHAFB#V0, R5F101GJAFB#V0, R5F101GKAFB#V0,
				R5F101GLAFB#V0
				R5F101GAAFB#X0, R5F101GCAFB#X0, R5F101GDAFB#X0,
				R5F101GEAFB#X0, R5F101GFAFB#X0, R5F101GGAFB#X0,
				R5F101GHAFB#X0, R5F101GJAFB#X0, R5F101GKAFB#X0,
				R5F101GLAFB#X0
			D	R5F101GADFB#V0, R5F101GCDFB#V0, R5F101GDDFB#V0,
				R5F101GEDFB#V0, R5F101GFDFB#V0, R5F101GGDFB#V0,
				R5F101GHDFB#V0, R5F101GJDFB#V0, R5F101GKDFB#V0,
				R5F101GLDFB#V0
				R5F101GADFB#X0, R5F101GCDFB#X0, R5F101GDDFB#X0,
				R5F101GEDFB#X0, R5F101GFDFB#X0, R5F101GGDFB#X0,
				R5F101GHDFB#X0, R5F101GJDFB#X0, R5F101GKDFB#X0,
				R5F101GLDFB#X0

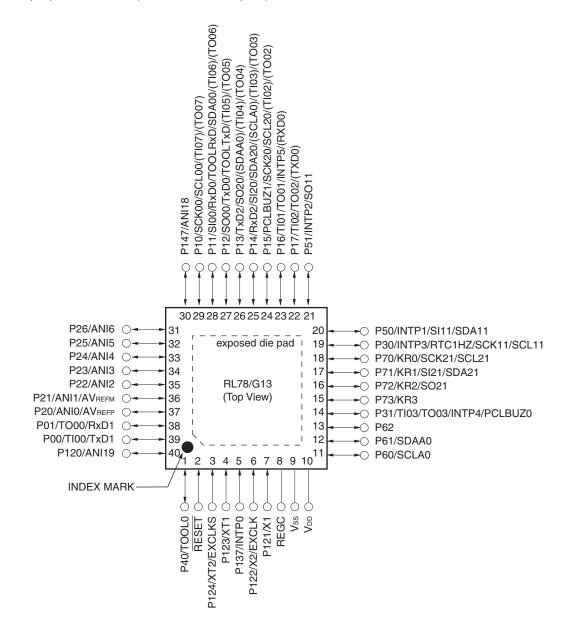
Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.



1.3.7 40-pin products

• 40-pin plastic HWQFN (6 × 6 mm, 0.5 mm pitch)





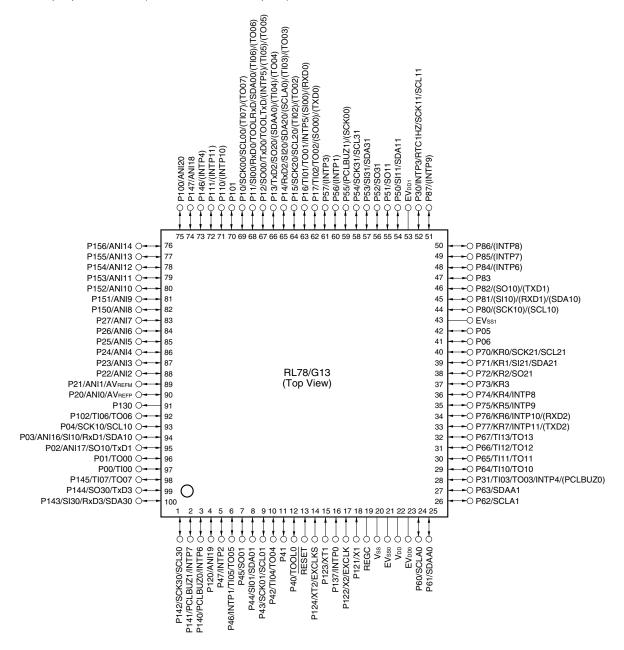
Remarks 1. For pin identification, see 1.4 Pin Identification.

- Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.
- 3. It is recommended to connect an exposed die pad to $V_{ss.}$



1.3.13 100-pin products

• 100-pin plastic LQFP (14 × 14 mm, 0.5 mm pitch)



Cautions 1. Make EVsso, EVss1 pins the same potential as Vss pin.

- 2. Make VDD pin the potential that is higher than EVDD0, EVDD1 pins (EVDD0 = EVDD1).
- 3. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).
- Remarks 1. For pin identification, see 1.4 Pin Identification.
 - 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the V_{DD}, EV_{DD0} and EV_{DD1} pins and connect the V_{SS}, EV_{SS0} and EV_{SS1} pins to separate ground lines.
 - **3.** Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.



[80-pin, 100-pin, 128-pin products]

Caution This outline describes the functions at the time when Peripheral I/O redirection register (PIOR) is set to 00H.

							(1/2)			
	Item	80-	•	100)-pin	128-pin				
		R5F100Mx	R5F101Mx	R5F100Px	R5F101Px	R5F100Sx	R5F101Sx			
Code flash m	emory (KB)	96 te	o 512	96 to 512		192 to 512				
Data flash me	emory (KB)	8	_	8	-	8	-			
RAM (KB)		8 to 3	2 Note 1	8 to 3	32 Note 1	16 to 5	32 Note 1			
Address space	e	1 MB								
Main system clock	High-speed system clock	HS (High-speed HS (High-speed LS (Low-speed	mic) oscillation, I main) mode: 1 I main) mode: 1 main) mode: 1 e main) mode: 1	to 20 MHz (V_{DD} to 16 MHz (V_{DD} to 8 MHz (V_{DD} =	= 2.4 to 5.5 V), 1.8 to 5.5 V),	(EXCLK)				
	High-speed on-chip oscillator	HS (High-speed main) mode: 1 to 32 MHz ($V_{DD} = 2.7$ to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz ($V_{DD} = 2.4$ to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz ($V_{DD} = 1.8$ to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz ($V_{DD} = 1.6$ to 5.5 V)								
Subsystem cl	ock	XT1 (crystal) os 32.768 kHz	cillation, externa	I subsystem cloc	k input (EXCLKS	i)				
Low-speed or	n-chip oscillator	15 kHz (TYP.)								
General-purp	ose register	(8-bit register × 8) × 4 banks								
Minimum inst	ruction execution time	0.03125 μ s (High-speed on-chip oscillator: f _{IH} = 32 MHz operation)								
		0.05 µs (High-speed system clock: f _{MX} = 20 MHz operation)								
		30.5 µs (Subsystem clock: fsub = 32.768 kHz operation)								
Instruction se	t	 Data transfer (8/16 bits) Adder and subtractor/logical operation (8/16 bits) Multiplication (8 bits × 8 bits) Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc. 								
I/O port	Total	7	74		92	1	20			
	CMOS I/O	(N-ch O.D. I/O	64 [EV _{DD} withstand le]: 21)	(N-ch O.D. I/O	82 [EV⊳⊳ withstand ge]: 24)	(N-ch O.D. I/O	10 [EV _{DD} withstand ge]: 25)			
	CMOS input		5		5		5			
	CMOS output		1		1		1			
	N-ch O.D. I/O (withstand voltage: 6 V)		4		4		4			
Timer	16-bit timer	12 cha	annels	12 ch	annels	16 ch	annels			
	Watchdog timer	1 cha	annel	1 ch	annel	1 cha	annel			
	Real-time clock (RTC)	1 cha	annel	1 ch	annel	1 cha	annel			
	12-bit interval timer (IT)	1 cha	annel	1 ch	annel	1 cha	annel			
	Timer output	12 channels (PWM outputs:	10 ^{Note 2})	12 channels (PWM outputs:	10 Note 2)	16 channels (PWM outputs: 14 Note 2)				
	RTC output	1 channel • 1 Hz (subsyster)	tem clock: fsuв =	32.768 kHz)						

Notes 1. The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F100xJ, R5F101xJ (x = M, P): Start address FAF00H

R5F100xL, R5F101xL (x = M, P, S): Start address F7F00H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library** for RL78 Family (R20UT2944).



 The number of PWM outputs varies depending on the setting of channels in use (the number of masters and slaves) (see 6.9.3 Operation as multiple PWM output function in the RL78/G13 User's Manual).

						1	(2/2)		
Item		80-pin		100			3-pin		
		R5F100Mx R5	F101Mx	R5F100Px	R5F101Px	R5F100Sx	R5F101Sx		
Clock output/buzz	er output	2 2 2							
		 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: fmain = 20 MHz operation) 256 Hz, 512 Hz, 1.024 kHz, 2.048 kHz, 4.096 kHz, 8.192 kHz, 16.384 kHz, 32.768 kHz (Subsystem clock: fsub = 32.768 kHz operation) 							
8/10-bit resolution	A/D converter	17 channels		20 channels		26 channels			
Serial interface		[80-pin, 100-pin, 128-	pin product	ts]					
		 CSI: 2 channels/sin 	nplified I ² C: nplified I ² C:	2 channels/UAR 2 channels/UAR	T: 1 channel T (UART suppor	ting LIN-bus): 1 c	channel		
	l ² C bus	2 channels		2 channels		2 channels			
Multiplier and divid	der/multiply-	• 16 bits × 16 bits = 32	2 bits (Unsi	igned or signed)					
accumulator		• 32 bits ÷ 32 bits = 32 bits (Unsigned)							
		• 16 bits × 16 bits + 32 bits = 32 bits (Unsigned or signed)							
DMA controller		4 channels							
Vectored	Internal	37		37		41			
interrupt sources	External	13		1	3	-	13		
Key interrupt	I	8		8 8		8			
Reset		 Reset by RESET pin Internal reset by watchdog timer Internal reset by power-on-reset Internal reset by voltage detector Internal reset by illegal instruction execution ^{Note} Internal reset by RAM parity error Internal reset by illegal-memory access 							
Power-on-reset ci	rcuit	 Power-on-reset: 1.51 V (TYP.) Power-down-reset: 1.50 V (TYP.) 							
Voltage detector		Rising edge : 1.67 V to 4.06 V (14 stages) Falling edge : 1.63 V to 3.98 V (14 stages)							
On-chip debug fur	nction	Provided							
Power supply voltage		$V_{_{DD}} = 1.6 \text{ to } 5.5 \text{ V} (T_{_{A}} = -40 \text{ to } +85^{\circ}\text{C})$ $V_{_{DD}} = 2.4 \text{ to } 5.5 \text{ V} (T_{_{A}} = -40 \text{ to } +105^{\circ}\text{C})$							
Operating ambien	t temperature	$T_A = 40$ to +85°C (A: Consumer applications, D: Industrial applications) $T_A = 40$ to +105°C (G: Industrial applications)							

<R>

Note The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution not issued by emulation with the in-circuit emulator or on-chip debug emulator.



Parameter	Symbols		Conditions	Ratings	Unit
Output current, high	Юн1	Per pin	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	-40	mA
		Total of all pins –170 mA	P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	-70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147	-100	mA
	Іон2	Per pin	P20 to P27, P150 to P156	-0.5	mA
		Total of all pins		-2	mA
Output current, low	Iol1	Per pin	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	40	mA
		Total of all pins 170 mA	P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147	100	mA
	IOL2	Per pin	P20 to P27, P150 to P156	1	mA
		Total of all pins			mA
Operating ambient	TA	In normal operati	on mode	-40 to +85	°C
temperature		In flash memory	programming mode		
Storage temperature	Tstg			-65 to +150	°C

Absolute Maximum Ratings (TA = 25°C) (2/2)

- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.
- **Remark** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



(3) 128-pin products, and flash ROM: 384 to 512 KB of 44- to 100-pin products

$(TA = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V}) (1/2)$

Parameter	Symbol			Conditions	-		MIN.	TYP.	MAX.	Unit
Supply	DD1	Operating	HS (high-	$f_{IH} = 32 \text{ MHz}^{Note 3}$	Basic	V _{DD} = 5.0 V		2.6		mA
current Note 1		mode	speed main) mode ^{Note 5}		operation	$V_{DD} = 3.0 V$		2.6		mA
					Normal	$V_{DD} = 5.0 V$		6.1	9.5	mA
					operation	$V_{DD} = 3.0 V$		6.1	9.5	mA
				$f_{IH} = 24 \text{ MHz}^{Note 3}$	Normal	$V_{DD} = 5.0 V$		4.8	7.4	mA
					operation	$V_{DD} = 3.0 V$		4.8	7.4	mA
				$f_{IH} = 16 \ MHz^{Note \ 3}$	Normal	$V_{DD} = 5.0 V$		3.5	5.3	mA
					operation	V _{DD} = 3.0 V		3.5	5.3	mA
			LS (low- speed main) mode ^{Note 5}	$f_{IH} = 8 \text{ MHz}^{Note 3}$	Normal	$V_{DD} = 3.0 V$		1.5	2.3	mA
					operation	$V_{DD} = 2.0 V$		1.5	2.3	mA
			LV (low- voltage main) mode	$f_{IH} = 4 \text{ MHz}^{Note 3}$	Normal	V _{DD} = 3.0 V		1.5	2.0	mA
					operation	V _{DD} = 2.0 V		1.5	2.0	mA
			HS (high-	f _{MX} = 20 MHz ^{Note 2} ,	Normal	Square wave input		3.9	6.1	mA
			speed main) mode ^{Note 5}	V _{DD} = 5.0 V	operation	Resonator connection		4.1	6.3	mA
				f _{MX} = 20 MHz ^{Note 2} ,	Normal	Square wave input		3.9	6.1	mA
				$V_{DD} = 3.0 V$		Resonator connection		4.1	6.3	mA
				$f_{MX} = 10 \text{ MHz}^{Note 2},$	Normal	Square wave input		2.5	3.7	mA
				$V_{DD} = 5.0 V$	operation	Resonator connection		2.5	3.7	mA
				$f_{MX} = 10 \text{ MHz}^{Note 2},$	Normal operation	Square wave input		2.5	3.7	mA
				$V_{DD} = 3.0 V$		Resonator connection		2.5	3.7	mA
			LS (low- speed main) mode ^{Note 5}	$f_{MX} = 8 \text{ MHz}^{Note 2},$	Normal	Square wave input		1.4	2.2	mA
				$V_{DD} = 3.0 V$	operation	Resonator connection		1.4	2.2	mA
				$f_{MX} = 8 \text{ MHz}^{Note 2},$	Normal	Square wave input		1.4	2.2	mA
				$V_{DD} = 2.0 V$	operation	Resonator connection		1.4	2.2	mA
			Subsystem	fsub = 32.768 kHz	Normal	Square wave input		5.4	6.5	μA
			clock operation	$T_A = -40^{\circ}C$	operation	Resonator connection		5.5	6.6	μA
				fsub = 32.768 kHz	Normal	Square wave input		5.5	6.5	μA
				$T_A = +25^{\circ}C$	operation	Resonator connection		5.6	6.6	μA
				fsub = 32.768 kHz	Normal	Square wave input		5.6	9.4	μA
				$T_{A} = +50^{\circ}C$	operation	Resonator connection		5.7	9.5	μA
				fsuв = 32.768 kHz	Normal operation	Square wave input		5.9	12.0	μA
				Note 4 $T_A = +70^{\circ}C$		Resonator connection		6.0	12.1	μA
				fsuв = 32.768 kHz	Normal	Square wave input		6.6	16.3	μA
				Note 4 $T_A = +85^{\circ}C$	operation	Resonator connection		6.7	16.4	μA

(Notes and Remarks are listed on the next page.)



Remarks 1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3),

g: PIM and POM numbers (g = 0, 1, 4, 5, 8, 14)

2. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

(4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) (1/2) ($T_A = -40$ to $+85^{\circ}$ C, 1.6 V \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 V, Vss = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Condit	Conditions		h-speed Mode	LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkCY2	$4.0~V \leq EV_{DD0} \leq 5.5$	20 MHz < fмск	8/fмск		_		_		ns
Note 5		V	fмск \leq 20 MHz	6/fмск		6/fмск		6/fмск		ns
		$2.7~V \leq EV_{\text{DD0}} \leq 5.5$	16 MHz < fмск	8/fмск		_		_		ns
		V	fмск \leq 16 MHz	6/fмск		6/fмск		6/fмск		ns
		$2.4~V \leq EV_{\text{DD0}} \leq 5.5~V$	$2.4 \text{ V} \leq EV_{\text{DD0}} \leq 5.5 \text{ V}$			6/fмск and 500		6/fмск and 500		ns
		$1.8 \text{ V} \leq EV_{\text{DD0}} \leq 5.5 \text{ V}$ $1.7 \text{ V} \leq EV_{\text{DD0}} \leq 5.5 \text{ V}$		6/fмск and 750		6/fмск and 750		6/fмск and 750		ns
				6/fмск and 1500		6/fмск and 1500		6/fмск and 1500		ns
		$1.6 \ V \leq EV_{\text{DD0}} \leq 5.5$	V	—		6/fмск and 1500		6/fмск and 1500		ns
SCKp high-/low- level width	tкн2, tкL2	$4.0~V \le EV_{DD0} \le 5.5~V$		tксү2/2 – 7		tксү2/2 - 7		tксү2/2 - 7		ns
		$2.7~V \leq EV_{DD0} \leq 5.5~V$	$2.7~V \leq EV_{\text{DD0}} \leq 5.5~V$			tксү2/2 - 8		tксү2/2 - 8		ns
		$1.8 V \le EV_{DD0} \le 5.5 V$	$1.8~V \leq EV_{DD0} \leq 5.5~V$			tксү2/2 – 18		tксү2/2 – 18		ns
		$1.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$	$1.7~V \leq EV_{\text{DD0}} \leq 5.5~V$			tксү2/2 - 66		tксү2/2 - 66		ns
		$1.6~V \leq EV_{\text{DD0}} \leq 5.5~V$		_		tксү2/2 - 66		tксү2/2 - 66		ns

(Notes, Caution, and Remarks are listed on the next page.)



Parameter	Symbol	Conditions	、 U	h-speed Mode	``	/-speed Mode	`	-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Data setup time (reception)	tsu:dat	$\label{eq:constraint} \begin{array}{l} 2.7~V \leq EV_{\text{DD0}} \leq 5.5~V, \\ C_{\text{b}} = 50~pF,~R_{\text{b}} = 2.7~k\Omega \end{array}$	1/fмск + 85 _{Note2}		1/fмск + 145 _{Note2}		1/fмск + 145 _{Note2}		ns
		$\label{eq:linear} \begin{split} 1.8 \ V &\leq EV_{\text{DD0}} \leq 5.5 \ V, \\ C_{\text{b}} &= 100 \ p\text{F}, \ R_{\text{b}} = 3 \ k\Omega \end{split}$	1/fмск + 145 _{Note2}		1/fмск + 145 _{Note2}		1/fмск + 145 _{Note2}		ns
		$\label{eq:linear} \begin{split} 1.8 \ V &\leq EV_{\text{DD0}} < 2.7 \ V, \\ C_{\text{b}} &= 100 \ p\text{F}, \ R_{\text{b}} = 5 \ k\Omega \end{split}$	1/fмск + 230 _{Note2}		1/f _{MCK} + 230 _{Note2}		1/fмск + 230 _{Note2}		ns
		$\label{eq:linear} \begin{array}{l} 1.7 \mbox{ V} \leq EV_{\mbox{\tiny DD0}} < 1.8 \mbox{ V}, \\ C_{\mbox{\tiny b}} = 100 \mbox{ pF}, \mbox{ R}_{\mbox{\tiny b}} = 5 \mbox{ k}\Omega \end{array}$	1/fмск + 290 _{Note2}		1/f _{MCK} + 290 _{Note2}		1/fмск + 290 _{Note2}		ns
		$\label{eq:linear} \begin{array}{l} 1.6 \mbox{ V} \leq EV_{\mbox{DD0}} < 1.8 \mbox{ V}, \\ C_{\mbox{\tiny b}} = 100 \mbox{ pF}, \mbox{ R}_{\mbox{\tiny b}} = 5 k\Omega \end{array}$	—		1/f _{MCK} + 290 _{Note2}		1/fмск + 290 _{Note2}		ns
Data hold time (transmission)	thd:dat	$\begin{array}{l} 2.7 \ \text{V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \ \text{V}, \\ \text{C}_{\text{b}} = 50 \ \text{pF}, \ \text{R}_{\text{b}} = 2.7 \ \text{k}\Omega \end{array}$	0	305	0	305	0	305	ns
		$\label{eq:linear} \begin{array}{l} 1.8 \mbox{ V} \leq EV_{\mbox{DD0}} \leq 5.5 \mbox{ V}, \\ C_{\mbox{\tiny b}} = 100 \mbox{ pF}, \mbox{ R}_{\mbox{\tiny b}} = 3 k\Omega \end{array}$	0	355	0	355	0	355	ns
		$\label{eq:linear} \begin{array}{l} 1.8 \mbox{ V} \leq EV_{\mbox{DD0}} < 2.7 \mbox{ V}, \\ C_{\mbox{\tiny b}} = 100 \mbox{ pF}, \mbox{ R}_{\mbox{\tiny b}} = 5 k\Omega \end{array}$	0	405	0	405	0	405	ns
		$1.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 1.8 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 5 \text{ k}\Omega$	0	405	0	405	0	405	ns
		$1.6 \text{ V} \leq \text{EV}_{\text{DD0}} < 1.8 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 5 \text{ k}\Omega$	_	_	0	405	0	405	ns

(5)	During communication at same potential (simplified I ² C mode) (2/2)
	$(T_{A} = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Notes 1. The value must also be equal to or less than $f_{MCK}/4$.

2. Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the normal input buffer and the N-ch open drain output (VDD tolerance (When 20- to 52-pin products)/EVDD tolerance (When 64- to 128-pin products)) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

(**Remarks** are listed on the next page.)



(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (3/3)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		/-speed Mode		-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↓) ^{Note 1}	tsıkı	$\begin{array}{l} 4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, \end{array}$	44		110		110		ns
		$\label{eq:cb} \begin{split} C_b &= 30 \; pF, \; R_b = 1.4 \; k\Omega \\ 2.7 \; V &\leq EV_{\text{DD0}} < 4.0 \; V, \\ 2.3 \; V &\leq V_b \leq 2.7 \; V, \end{split}$	44		110		110		ns
		C_b = 30 pF, R_b = 2.7 k Ω							
		$\label{eq:VDD} \begin{split} 1.8 \ V &\leq EV_{\text{DD0}} < 3.3 \ V, \\ 1.6 \ V &\leq V_b \leq 2.0 \ V^{\text{Note 2}}, \end{split}$	110		110		110		ns
		$C_{b}=30 \text{ pF}, \text{R}_{b}=5.5 \text{k}\Omega$							
SIp hold time (from SCKp↓) ^{№ te 1}	tksii	$\begin{array}{l} 4.0 \ V \leq EV_{\text{DD0}} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, \end{array}$	19		19		19		ns
		$C_{b}=30 \text{ pF}, \text{R}_{b}=1.4 \text{k}\Omega$							
		$\begin{array}{l} 2.7 \ V \leq EV_{\text{DD0}} < 4.0 \ V, \\ 2.3 \ V \leq V_{b} \leq 2.7 \ V, \end{array}$	19		19		19		ns
		$C_{b}=30 \text{ pF}, \text{R}_{b}=2.7 \text{k}\Omega$							
		$ \begin{array}{l} 1.8 \ V \leq EV_{\text{DD0}} < 3.3 \ V, \\ 1.6 \ V \leq V_{b} \leq 2.0 \ V^{\text{Note 2}}, \end{array} $	19		19		19		ns
		$C_{b}=30 \text{ pF}, \text{R}_{b}=5.5 \text{k}\Omega$							
Delay time from SCKp↑ to	tkso1	$ \begin{array}{l} 4.0 \ V \leq EV_{\text{DD0}} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, \end{array} $		25		25		25	ns
SOp output Note 1		$C_{b}=30 \text{ pF}, \text{R}_{b}=1.4 \text{k}\Omega$							
		$\begin{array}{l} 2.7 \ V \leq EV_{\rm DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_{\rm b} \leq 2.7 \ V, \end{array}$		25		25		25	ns
		$C_{b}=30 \text{ pF}, \text{R}_{b}=2.7 \text{k}\Omega$							
		$\label{eq:linear} \begin{split} 1.8 \ V &\leq EV_{\text{DD0}} < 3.3 \ V, \\ 1.6 \ V &\leq V_b \leq 2.0 \ V^{\text{Note 2}}, \end{split}$		25		25		25	ns
		$C_{b}=30 \text{ pF}, \text{R}_{b}=5.5 \text{k}\Omega$							

		5 5 V Voo - EVo	$ = EV_{oot} = 0.V$
$T_{A} = -40$ to +85°C,		j.j v, vss = ⊑vs	$s_0 = \Box v s s_1 = U v $

Notes 1. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

2. Use it with $EV_{DD0} \ge V_b$.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (When 20- to 52-pin products)/EVDD tolerance (When 64- to 128-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)



2.6.2 Temperature sensor/internal reference voltage characteristics

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	VTMPS25	Setting ADS register = 80H, $T_A = +25^{\circ}C$		1.05		V
Internal reference voltage	VBGR	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	Fvtmps	Temperature sensor that depends on the temperature		-3.6		mV/°C
Operation stabilization wait time	tamp		5			μs

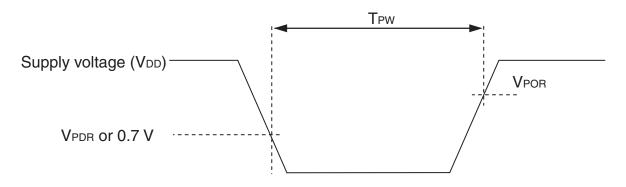
(TA = -40 to +85°C, 2.4 V \leq V_{DD} \leq 5.5 V, V_{SS} = 0 V, HS (high-speed main) mode)

2.6.3 POR circuit characteristics

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	VPOR	POR Power supply rise time		1.51	1.55	V
	VPDR	Power supply fall time	1.46	1.50	1.54	V
Minimum pulse width ^{Note}	Tpw		300			μS

Note Minimum time required for a POR reset when V_{DD} exceeds below V_{PDR}. This is also the minimum time required for a POR reset from when V_{DD} exceeds below 0.7 V to when V_{DD} exceeds V_{POR} while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).





Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply	DD2	HALT	HS (high-	$f_{IH} = 32 \text{ MHz}^{Note 4}$	V _{DD} = 5.0 V		0.62	3.40	mA
Current	Note 2	mode	speed main) mode ^{Note 7}		V _{DD} = 3.0 V		0.62	3.40	mA
			mode	fin = 24 MHz ^{Note 4}	V _{DD} = 5.0 V		0.50	2.70	mA
					V _{DD} = 3.0 V		0.50	2.70	mA
				fi⊢ = 16 MHz ^{Note 4}	V _{DD} = 5.0 V		0.44	1.90	mA
					V _{DD} = 3.0 V		0.44	1.90	mA
			HS (high-	$f_{MX} = 20 \text{ MHz}^{Note 3},$	Square wave input		0.31	2.10	mA
			speed main) mode ^{Note 7}	$V_{DD} = 5.0 V$	Resonator connection		0.48	2.20	mA
		$f_{MX} = 20 \text{ MHz}^{Note 3},$	Square wave input		0.31	2.10	mA		
				$V_{DD} = 3.0 V$	Resonator connection		0.48	2.20	mA
		$f_{MX} = 10 \text{ MHz}^{Note 3},$	Square wave input		0.21	1.10	mA		
				$V_{DD} = 5.0 V$	Resonator connection		0.28	1.20	mA
				$f_{MX} = 10 \text{ MHz}^{Note 3},$	Square wave input		0.21	1.10	mA
				$V_{DD} = 3.0 V$	Resonator connection		0.28	1.20	mA
			Subsystem	fsub = 32.768 kHz ^{Note 5}	Square wave input		0.28	0.61	μA
			clock operation	$T_A = -40^{\circ}C$	Resonator connection		0.47	0.80	μA
		fsub = 32.768 kHz ^{Note 5}	Square wave input		0.34	0.61	μA		
				T _A = +25°C	Resonator connection		0.53	0.80	μA
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.41	2.30	μA
				$T_A = +50^{\circ}C$	Resonator connection		0.60	2.49	μA
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.64	4.03	μA
				$T_A = +70^{\circ}C$	Resonator connection		0.83	4.22	μA
				$f_{SUB} = 32.768 \text{ kHz}^{Note 5}$	Square wave input		1.09	8.04	μA
				T _A = +85°C	Resonator connection		1.28	8.23	μA
				fsue = 32.768 kHz ^{Note 5}	Square wave input		5.50	41.00	μA
				T _A = +105°C	Resonator connection		5.50	41.00	μA
		STOP	$T_A = -40^{\circ}C$				0.19	0.52	μA
		mode ^{Note 8}	T _A = +25°C				0.25	0.52	μA
			T _A = +50°C				0.32	2.21	μA
			T _A = +70°C				0.55	3.94	μA
			T _A = +85°C				1.00	7.95	μA
			T _A = +105°C				5.00	40.00	μA

(2) Flash ROM: 96 to 256 KB of 30- to 100-pin products	
$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ V}_{DD1} \le 100 \text{ V}_{DD1} \le 1000 \text{ V}_{DD1} \le 100 \text{ V}_{DD1} = 100 $	$V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) (2/2)$

(Notes and Remarks are listed on the next page.)



(2)	During communication at same potential (CSI mode) (master mode, SCKp internal clock output)
	$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD}} = \text{EV}_{\text{DD}} \le 5.5 \text{ V}, \text{ Vss} = \text{EV}_{\text{SS}} = \text{EV}_{\text{SS}} = 0 \text{ V})$

Parameter	Symbol	Conditions		HS (high-spee	HS (high-speed main) Mode	
				MIN.	MAX.	
SCKp cycle time	tkCY1	$t_{KCY1} \geq 4/f_{CLK}$	$2.7~V \leq EV_{\text{DD0}} \leq 5.5~V$	250		ns
			$2.4~V \leq EV_{\text{DD0}} \leq 5.5~V$	500		ns
SCKp high-/low-level width	tкнı,	$4.0~V \leq EV_{DD0} \leq 5.5~V$		tксү1/2 – 24		ns
	tĸ∟ı	$2.7~V \leq EV_{\text{DD0}} \leq 5.5~V$		tксү1/2 – 36		ns
		$2.4~V \leq EV_{\text{DD0}} \leq 5.5~V$		tксү1/2 – 76		ns
SIp setup time (to SCKp↑) ^{Note 1}	tsıкı	$4.0~V \leq EV_{\text{DD0}} \leq 5.5~V$		66		ns
		$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$		66		ns
		$2.4 \ V \le EV_{DD}$	$_{0} \leq 5.5 \text{ V}$	113		ns
SIp hold time (from SCKp^) $^{\mbox{Note 2}}$	tksi1			38		ns
Delay time from SCKp↓ to SOp output ^{Note 3}	tkso1	C = 30 pF Note 4			50	ns

- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to $SCKp\downarrow$ " when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp[↑]" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SCKp and SOp output lines.
- Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).
- **Remarks 1.** p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3),

g: PIM and POM numbers (g = 0, 1, 4, 5, 8, 14)

2. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03, 10 to 13))



Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
SCLr clock frequency	fscL	$2.7~V \leq EV_{\text{DD0}} \leq 5.5~V,$		400 Note1	kHz
		$C_b = 50 \text{ pF}, \text{ R}_b = 2.7 \text{ k}\Omega$			
		$2.4~V \leq EV_{\text{DD0}} \leq 5.5~V,$		100 Note1	kHz
		$C_b = 100 \text{ pF}, \text{ R}_b = 3 \text{k}\Omega$			
Hold time when SCLr = "L"	t∟ow	$2.7~V \leq EV_{\text{DD0}} \leq 5.5~V,$	1200		ns
		$C_b = 50 \text{ pF}, \text{ R}_b = 2.7 \text{ k}\Omega$			
		$2.4~V \leq EV_{\text{DD0}} \leq 5.5~V,$	4600		ns
		$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$			
Hold time when SCLr = "H"	tніgн	$2.7~V \leq EV_{\text{DD0}} \leq 5.5~V,$	1200		ns
		$C_b = 50 \text{ pF}, \text{R}_b = 2.7 \text{ k}\Omega$			
		$2.4~V \leq EV_{\text{DD0}} \leq 5.5~V,$	4600		ns
		$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$			
Data setup time (reception)	tsu:dat	$2.7~V \leq EV_{\text{DD0}} \leq 5.5~V,$	1/fмск + 220		ns
		$C_b = 50 \text{ pF}, \text{ R}_b = 2.7 \text{ k}\Omega$	Note2		
		$2.4~V \leq EV_{\text{DD}} \leq 5.5~V,$	1/fмск + 580		ns
		$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$	Note2		
Data hold time (transmission)	thd:dat	$2.7~V \leq EV_{\text{DD0}} \leq 5.5~V,$	0	770	ns
		C_b = 50 pF, R_b = 2.7 k Ω			
		$2.4~V \leq EV_{\text{DD0}} \leq 5.5~V,$	0	1420	ns
		$C_b = 100 \text{ pF}, \text{ R}_b = 3 \text{k}\Omega$			

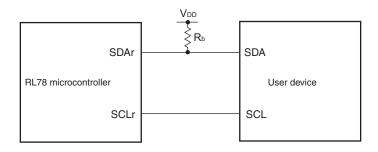
(4) During communication at same potential (simplified l²C mode) (T_A = -40 to +105°C, 2.4 V \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 V, Vss = EV_{SS0} = EV_{SS1} = 0 V)

- Notes 1. The value must also be equal to or less than $f_{MCK}/4$.
 - **2.** Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H".
- Caution Select the normal input buffer and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

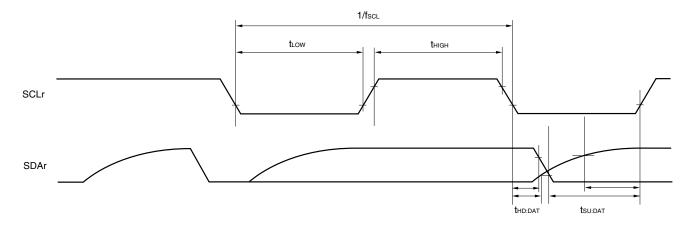
(Remarks are listed on the next page.)



Simplified I²C mode mode connection diagram (during communication at same potential)



Simplified I²C mode serial transfer timing (during communication at same potential)



- **Remarks 1.** R_b[Ω]:Communication line (SDAr) pull-up resistance, C_b[F]: Communication line (SDAr, SCLr) load capacitance
 - r: IIC number (r = 00, 01, 10, 11, 20, 21, 30, 31), g: PIM number (g = 0, 1, 4, 5, 8, 14),
 h: POM number (g = 0, 1, 4, 5, 7 to 9, 14)
 - 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m

= 0, 1), n: Channel number (n = 0 to 3), mn = 00 to 03, 10 to 13)



(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp int	ernal clock
output) (1/3)	

Parameter	Symbol		Conditions	HS (high-spee	d main) Mode	Unit
				MIN.	MAX.	
SCKp cycle time	tксүı	$\begin{array}{l} t_{\text{KCY1}} \geq 4/f_{\text{CLK}} & 4.0 \ \text{V} \leq EV_{\text{DD0}} \leq 5.5 \ \text{V}, \ 2.7 \ \text{V} \leq V_b \leq 4.0 \\ \\ \text{V}, \\ \\ C_b = 30 \ \text{pF}, \ R_b = 1.4 \ \text{k}\Omega \end{array}$		600		ns
			$\begin{array}{l} 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \; 2.3 \; V \leq V_b \leq 2.7 \\ V, \\ C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	1000		ns
			$\begin{array}{l} 2.4 \ V \leq EV_{DD0} < 3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \\ V, \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$	2300		ns
SCKp high-level width	tкнı		$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$ $C_{\text{b}} = 30 \text{ pF}, \text{ R}_{\text{b}} = 1.4 \text{ k}\Omega$ $2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 30 \text{ pF}, \text{ R}_{\text{b}} = 2.7 \text{ k}\Omega$			ns
						ns
		$2.4 \text{ V} \leq \text{EV}_{\text{DD}}$ $C_{\text{b}} = 30 \text{ pF}, \text{ F}$	$_{0}$ < 3.3 V, 1.6 V \leq V $_{b}$ \leq 2.0 V, R $_{b}$ = 5.5 k Ω	tксү1/2 – 916		ns
SCKp low-level width	tĸ∟1					ns
		$2.7 \text{ V} \leq \text{EV}_{\text{DD}}$ $C_{\text{b}} = 30 \text{ pF}, \text{ F}$	$_{0}$ < 4.0 V, 2.3 V \leq V _b \leq 2.7 V, R _b = 2.7 k Ω	tксү1/2 – 36		ns
			$2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V},$ $C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 5.5 \text{ k}\Omega$			ns

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD}0} = \text{EV}_{\text{DD}1} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(**Remarks** are listed two pages after the next page.)



(7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
SCKp cycle time Note 1	tксү2	$4.0~V \leq EV_{\text{DD0}} \leq 5.5$	24 MHz < fмск	28/f мск		ns
		V,	$20 \text{ MHz} < f_{MCK} \le 24 \text{ MHz}$	24/f мск		ns
		$2.7 \ V {\leq} V_b {\leq} 4.0 \ V$	8 MHz < fмск ≤ 20 MHz	20/f мск		ns
			$4 \text{ MHz} < f_{\text{MCK}} \le 8 \text{ MHz}$	16/f мск		ns
			fмск \leq 4 MHz	12/f мск		ns
		$2.7~V \leq EV_{DD0} < 4.0$	24 MHz < fмск	40/f мск		ns
		V,	$20 \text{ MHz} < f_{MCK} \le 24 \text{ MHz}$	32/f мск		ns
		$2.3V{\leq}V_b{\leq}2.7V$	$16 \text{ MHz} < f_{MCK} \le 20 \text{ MHz}$	28/f мск		ns
			$8 \text{ MHz} < f_{\text{MCK}} \le 16 \text{ MHz}$	24/fмск		ns
			$4 \text{ MHz} < f_{\text{MCK}} \le 8 \text{ MHz}$	16/f мск		ns
			fмск \leq 4 MHz	12/fмск		ns
		$2.4~V \leq EV_{\text{DD0}} < 3.3$	24 MHz < fмск	96/f мск		ns
		V,	$20 \text{ MHz} < f_{MCK} \le 24 \text{ MHz}$	72/f мск		ns
		$1.6 V \le V_b \le 2.0 V$	$16 \text{ MHz} < f_{\text{MCK}} \le 20 \text{ MHz}$	64/f мск		ns
			$8 \text{ MHz} < f_{\text{MCK}} \le 16 \text{ MHz}$	52/f мск		ns
			4 MHz < fмск ≤ 8 MHz	32/ fмск		ns
			fмск \leq 4 MHz	20/fмск		ns
SCKp high-/low-level width	tкн2, tкL2	$\begin{array}{l} 4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V \\ \hline \\ 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V \end{array}$		tkcy2/2 - 24		ns
				tkcy2/2 - 36		ns
		$\begin{array}{l} 2.4 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V^{\text{Note 2}} \end{array}$		tkcy2/2 - 100		ns
SIp setup time (to SCKp↑) ^{Note2}	tsik2	$\begin{array}{l} 4.0 \; V \leq EV_{\text{DD0}} \leq 5. \\ 2.7 \; V \leq V_b \leq 4.0 \; V \end{array}$		1/fмск + 40		ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V \end{array}$		1/fмск + 40		ns
		$\label{eq:states} \begin{array}{l} 2.4 \ V \leq EV_{\text{DD0}} < 3. \\ 1.6 \ V \leq V_{\text{b}} \leq 2.0 \ V \end{array}$		1/fмск + 60		ns
SIp hold time (from SCKp↑) ^{№te 3}	tksi2			1/fмск + 62		ns
Delay time from SCKp↓ to SOp output ^{№te 4}	tkso2				2/fмск + 240	ns
		$\label{eq:constraint} \begin{array}{l} 2.7 \ V \leq EV_{\text{DD0}} < 4. \\ C_{\text{b}} = 30 \ \text{pF}, \ R_{\text{b}} = 2 \end{array}$	0 V, 2.3 V \leq V _b \leq 2.7 V, 2.7 kΩ		2/fмск + 428	ns
			3 V, 1.6 V \leq Vb \leq 2.0 V		2/fмск + 1146	ns

(Notes, Caution and Remarks are listed on the next page.)



4.11 64-pin Products

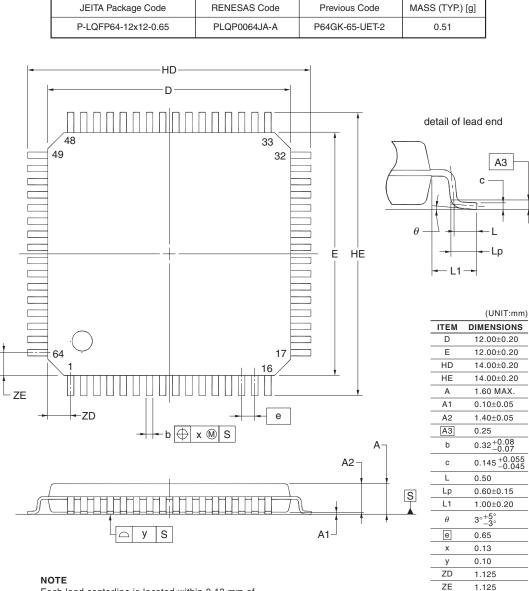
R5F100LCAFA, R5F100LDAFA, R5F100LEAFA, R5F100LFAFA, R5F100LGAFA, R5F100LHAFA, R5F100LJAFA, R5F100LLAFA

R5F101LCAFA, R5F101LDAFA, R5F101LEAFA, R5F101LFAFA, R5F101LGAFA, R5F101LHAFA, R5F101LJAFA, R5F101LLAFA

R5F100LCDFA, R5F100LDDFA, R5F100LEDFA, R5F100LFDFA, R5F100LGDFA, R5F100LHDFA, R5F100LJDFA, R5F100LLDFA

R5F101LCDFA, R5F101LDDFA, R5F101LEDFA, R5F101LFDFA, R5F101LGDFA, R5F101LHDFA, R5F101LJDFA, R5F101LLDFA

R5F100LCGFA, R5F100LDGFA, R5F100LEGFA, R5F100LFGFA, R5F100LGGFA, R5F100LHGFA, R5F100LJGFA



Each lead centerline is located within 0.13 mm of its true position at maximum material condition.

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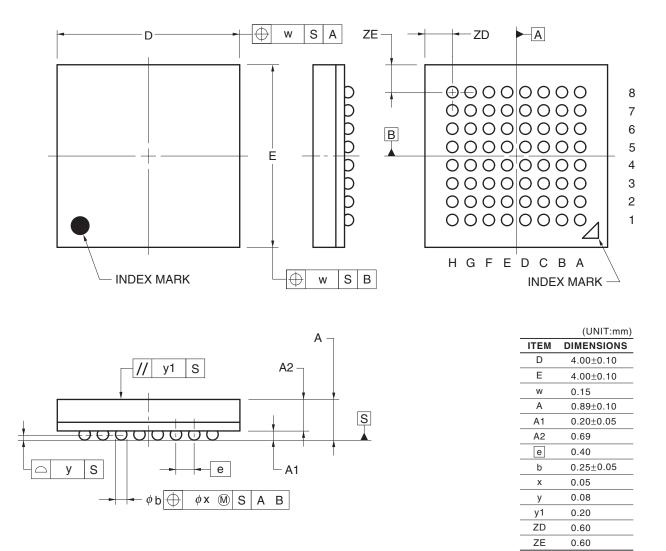


R5F100LCABG, R5F100LDABG, R5F100LEABG, R5F100LFABG, R5F100LGABG, R5F100LHABG, R5F100LJABG

R5F101LCABG, R5F101LDABG, R5F101LEABG, R5F101LFABG, R5F101LGABG, R5F101LHABG, R5F101LJABG

R5F100LCGBG, R5F100LDGBG, R5F100LEGBG, R5F100LFGBG, R5F100LGGBG, R5F100LHGBG, R5F100LJGBG

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-VFBGA64-4x4-0.40	PVBG0064LA-A	P64F1-40-AA2-2	0.03



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			Description
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3.00	Aug 02, 2013	118	Modification of table in 2.6.2 Temperature sensor/internal reference voltage characteristics
		118	Modification of table and note in 2.6.3 POR circuit characteristics
		119	Modification of table in 2.6.4 LVD circuit characteristics
		120	Modification of table of LVD Detection Voltage of Interrupt & Reset Mode
		120	Renamed to 2.6.5 Power supply voltage rising slope characteristics
		122	Modification of table, figure, and remark in 2.10 Timing Specs for Switching Flash Memory Programming Modes
		123	Modification of caution 1 and description
		124	Modification of table and remark 3 in Absolute Maximum Ratings ($T_A = 25^{\circ}C$)
		126	Modification of table, note, caution, and remark in 3.2.1 X1, XT1 oscillator characteristics
		126	Modification of table in 3.2.2 On-chip oscillator characteristics
		127	Modification of note 3 in 3.3.1 Pin characteristics (1/5)
		128	Modification of note 3 in 3.3.1 Pin characteristics (2/5)
		133	Modification of notes 1 and 4 in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products (1/2)
		135	Modification of notes 1, 5, and 6 in (1) Flash ROM: 16 to 64 KB of 20- to 64- pin products (2/2)
		137	Modification of notes 1 and 4 in (2) Flash ROM: 96 to 256 KB of 30- to 100- pin products (1/2)
		139	Modification of notes 1, 5, and 6 in (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products (2/2)
		140	Modification of (3) Peripheral Functions (Common to all products)
		142	Modification of table in 3.4 AC Characteristics
		143	Addition of Minimum Instruction Execution Time during Main System Clock Operation
		143	Modification of figure of AC Timing Test Points
		143	Modification of figure of External System Clock Timing
		145	Modification of figure of AC Timing Test Points
		145	Modification of description, note 1, and caution in (1) During communication at same potential (UART mode)
		146	Modification of description in (2) During communication at same potential (CSI mode)
		147	Modification of description in (3) During communication at same potential (CSI mode)
		149	Modification of table, note 1, and caution in (4) During communication at same potential (simplified I ² C mode)
		151	Modification of table, note 1, and caution in (5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2)
		152 to 154	Modification of table, notes 2 to 6, caution, and remarks 1 to 4 in (5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)
		155	Modification of table in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (1/3)
		156	Modification of table and caution in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (2/3)
		157, 158	Modification of table, caution, and remarks 3 and 4 in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (3/3)
		160, 161	Modification of table and caution in (7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode)